

Туре	Ag [*] Aİ [*]	V _{DRM} / V _{RRM}	V _{DSM} / V _{RSM} [V]	<i>I_{Т(AV)}</i> [А]	Chip Size [mm] x [mm]	Package Options	• •
CWP 347-	16 🗹 🗌	1600	1700	386	23.40 23.4	sawn on foil vnsawn wafer vin waffle pack v	
	*Frontside options					*Please contact IXYS chip sales	

Mechanical Parameters

Area active Area total Wafer size Ø Thickness Material Max. possible chips per wafer Passivation front side Metallization top side top side Recom. wire bonds (AI) Number / Ø [µm] Metallization backside Reject Ink Dot Size Recom. Storage Environment sawn on foil unsawn wafer in waffle pack

4.07 cm ²
5.48 cm ²
150 mm
380 μm
Si
21
Glassivation
solderable: Ti / Ni / Ag *
bondable: Al

Cathode Gate
/
solderable (only): Ti / Ni / Ag *

Ø 0.4-1.0 mm

Features

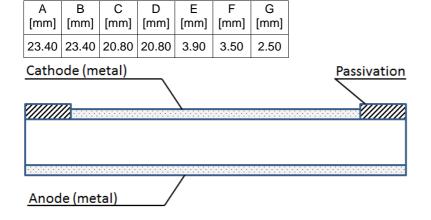
- planar design (non-mesa)
- ultra rugged for easy assembly (flat backside)
- excellent long term stability
- very low leakage current
- very low forward voltage drop

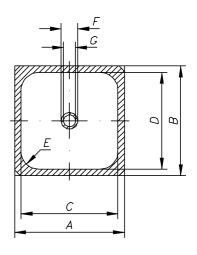
Applications

- DC motor control
- AC power control
- Softstrart AC motor controller
- Light, heat and temperature control
- Solid state relays
- Controlled rectifier circuits

*Sinterable top/bottom side on request

Dimensions







	Ratings					
Symbol	Conditions	min.	typ.	max.		
I _R	$V_D = Vr = Vrr$	$T_{vJ} = 25^{\circ}C$		0.5	mΑ	
		$T_{VJ} = 150^{\circ}C$		60	m/	
V ₇	I _T =600 A	$T_{VJ} = 25 ^{\circ}\text{C}$	1	1.16	\	
		T _{VJ} = 150 °C		1.11	\	
$V_{\tau o}$	For power-loss	s calculations only		0.85	V	
<i>r</i> ,	T _{vJ} = 150 °C			0.40	mΩ	
V _{G7}	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$	10	2	١	
		$T_{VJ} = -40$ °C		3	\	
I _{G7}	$V_D = 6 V$	$T_{v_J} = 25^{\circ}C$ 42		145	mΑ	
		$T_{VJ} = -40$ °C		220	mΑ	
V_{GD}	$T_{VJ} = 150 ^{\circ}\text{C}$	$V = \frac{2}{3} V_{DRM}$		0.25	١	
I _{GD}				10	m/	
I _L	t _p =30 μs	$T_{VJ} = 25^{\circ}\text{C}$ $I_{G} = 0.45 \text{ A}$ $di_{G}/dt = 0.45 \text{ A}/\mu\text{s}$		200	m/	
I _H	R _{GK} = ∞	$T_{VJ} = 25^{\circ}C$ $V_{D} = 6 \text{ V}$		150	m/	
t _{gd}		T _{v.i} = 25°C		2	μ	
-	- 5	$di_{G}/dt = 0.5 A/\mu$			•	
t _q		I _τ = 600 A -di/dt = 10 A/μs		200	μ	
*4	$t_{p} = 200 \mu s$	·				
(di/dt) _{cr}	repetitive	I _T = 750 A		100	A/µs	
	non repetitive	·			A/µs	
	$V = \frac{2}{3} V_{DRM}$	$T_{y_J} = 150 ^{\circ}\text{C}$ $di_g/dt = 0.45 \text{A/}\mu\text{s}$			•	
	$I_{\rm G} = 0.45 \text{A}$					
(dv/dt) _{cr}	-	$V_{DR} = \frac{2}{3} V_{DRM}$		1000	V/µs	
	R _{GK} = ∞	method 1 (linear voltage rise)			•	
P _{GM}	T _{V.I} = 150 °C	$t_p = 30 \mu s$		120	W	
	VJ	$t_p = 5E \mu s$		60	W	
$P_{\scriptscriptstyle GAV}$				20	W	
V _{RGM}				10	٧	
T _{VJ}		-40		150	°C	
I _{T(AV)}	$T_{c} = 100 ^{\circ}C$	180° rect.		386	Δ	
- 1(AV)	T _{vJ} = °C	180° sine		tbd	A	
I _{TSM} *	T _{v.i} = 45°C	t = 10 ms (50) Hz, sine		9500	Α	
	$V_R = 0 V$	t = 8.3 ms (60) Hz, sine		10300	Δ	
	T _{v.i} = 150 °C			8200	Α	
	$V_R = 0 V$	t = 8.3 ms (60) Hz, sine		8900	Α	
Pt *		t = 10 ms (50) Hz, sine		451250	Α :	
	$V_R = 0 V$	•				
	T _{VJ} = 150 °C	t = 10 ms (50) Hz, sine		440274 336200	A s	
	$V_R = 0 V$	t = 8.3 ms (60) Hz, sine t = 8.3 ms (60) Hz, sine		328722	AS	
R _{thJC} *	DC current		0.112	3-0,	K/W	

^{*} Data according to assembled product



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- the conclusion of quality agreements;
- to establish joint measures to ensure application specific product capabilities and notify that IXYS may delivery dependent on the realization of any such measures.